PRELIMINARY SPECIFICATION

NEC ELECTRON DEVICE

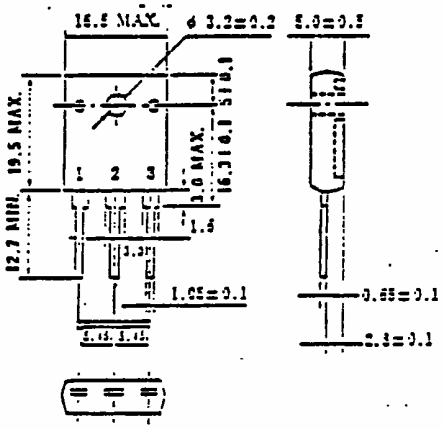
MOS FIELD EFFECT POWER TRANSISTOR

2SK719

FAST SWITCHING N-CHANNEL SILICON POWER MOS FET

PACKAGE DIMENSIONS

in millimeters



1 Gate

2 Drain

3 Source

FEATURES

- Suitable for switching power supplies, actuater controls and pulse circuits
- Low RDS(on)
- No second breakdown

ABSOLUTE MAXIMUM RATINGS (Ta=25 °C)

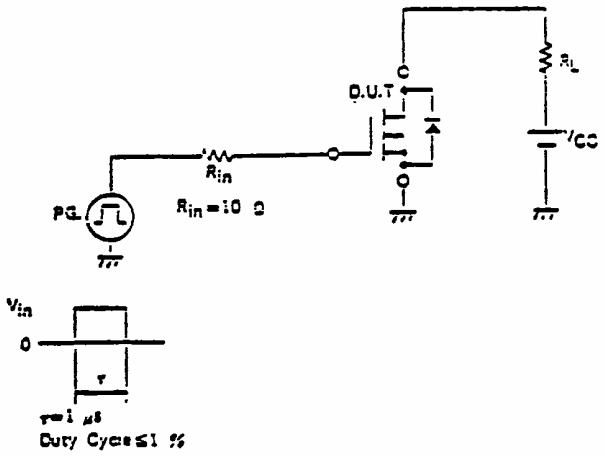
Drain to Source Voltage	VDSS	900V
Gate to Source Voltage	VGSS	±20V
Continuous Drain Current	ID(DC)	±5A
Total Power Dissipation	PT*	120W
Channel Temperature	Tch	150°C
Storage Temperature	Tstg	-55~150 °C

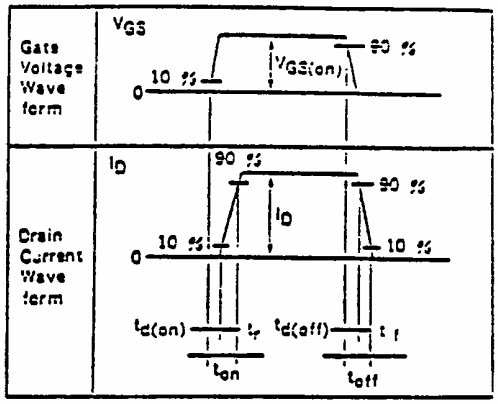
*Tc=25°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

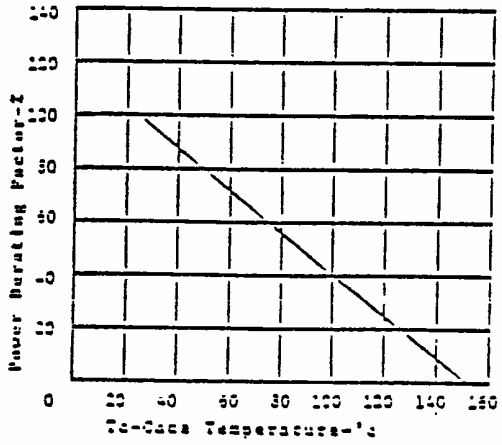
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain Leakage Current	IDSS			100	μA	VDS=900V, VGS=0
Gate to Source Leakage Current	IGSS			±100	nA	VGS=±20V, VDS=0
Gate to Source Cutoff Voltage	VGS(off)	1.5		3.5	V	VDS=10V, ID=1mA
Forward Transfer Admittance	|yfs|	1.0	2.5		S	VDS=20V, ID=3.0A
Drain to source On-State Resistance	RDS(on)		3.2	4.0	Ω	VGS=10V, ID=3.0A
Input Capacitance	Ciss		950		pF	VDS=10V
Output Capacitance	Coss		170		pF	VGS=0
Reverse Transfer Capacitance	Crss		65		pF	f=1MHz
Turn-On Delay Time	td(on)		15		ns	ID=3.0A, Vcc≒150V
Rise Time	tr		40		ns	VGS(on)=10V
Turn-Off Delay Time	td(off)		80		ns	RL=50Ω
Fall Time	tf		20		ns	

TURN-ON AND TURN-OFF TIME TEST CIRCUIT

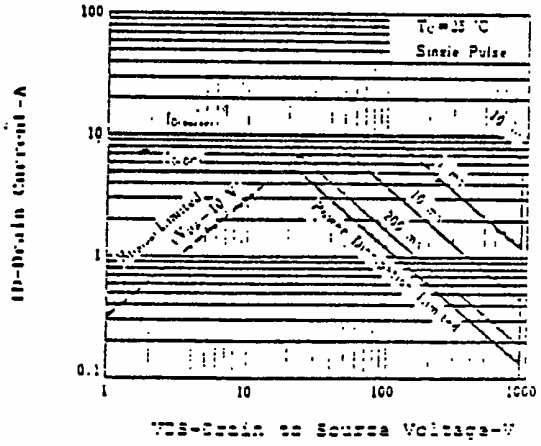




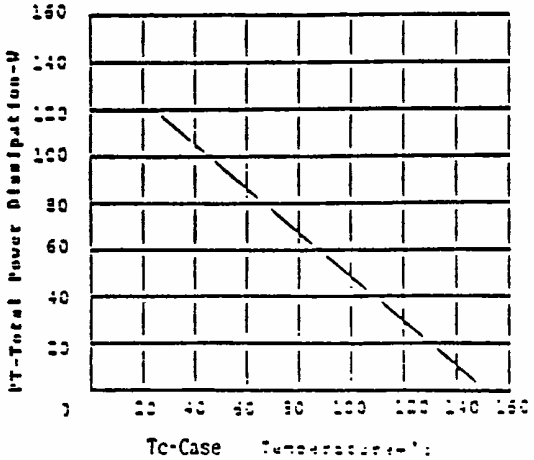
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



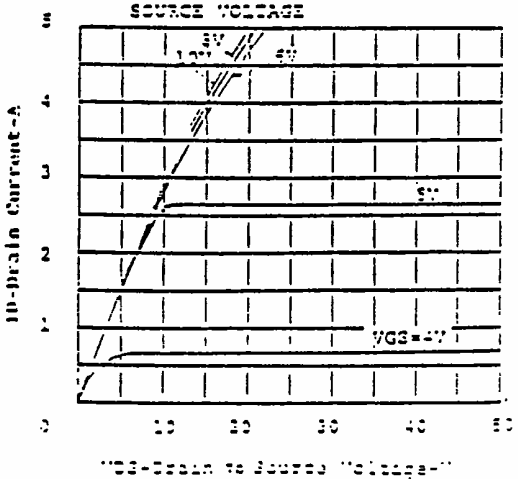
FORWARD BIAS SAFE OPERATING AREA



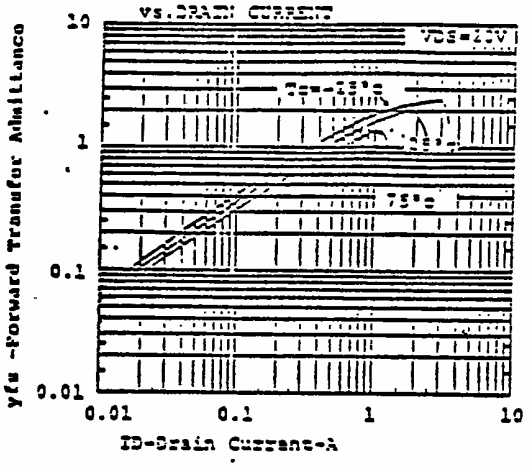
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



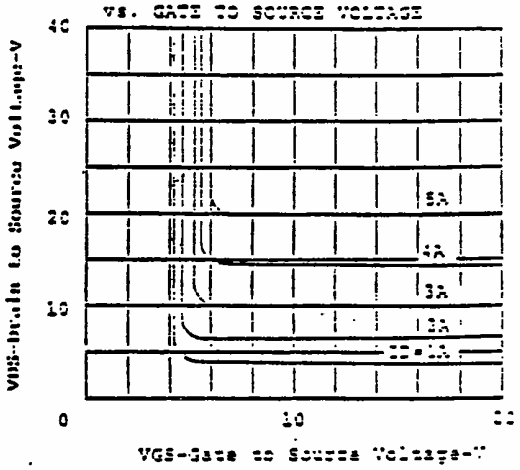
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



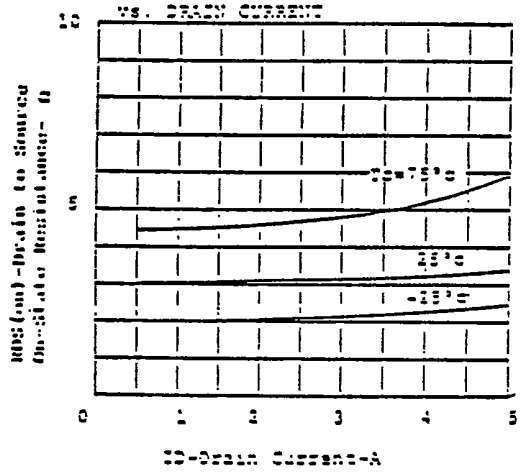
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



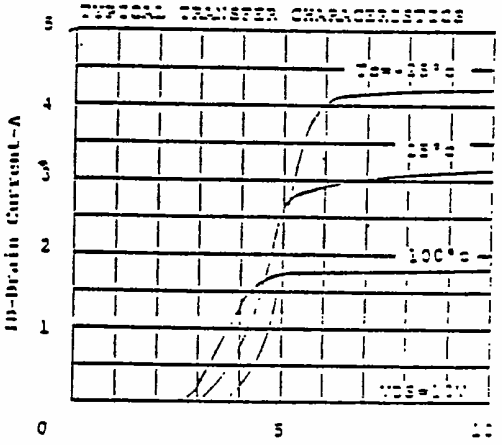
DRAIN TO SOURCE SATURATION VOLTAGE vs. GATE TO SOURCE VOLTAGE



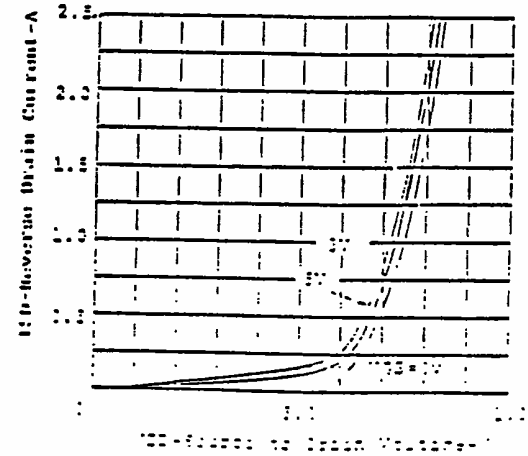
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



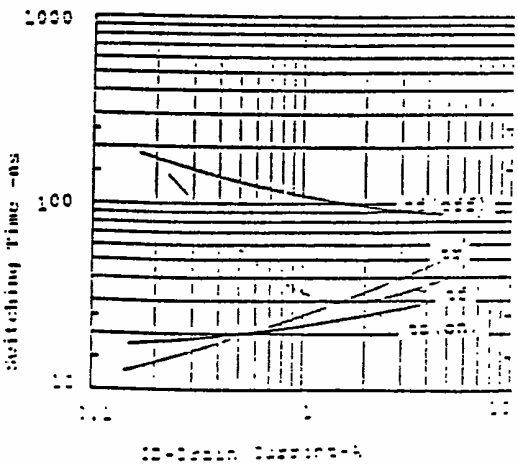
TYPICAL TRANSFER CHARACTERISTICS



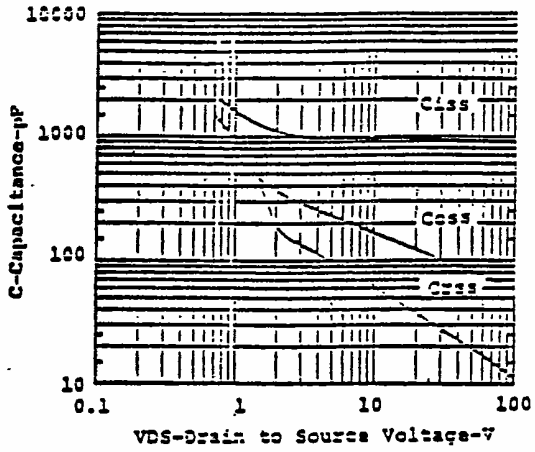
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



SWITCHING CHARACTERISTICS



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



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